

1 ABSTRACT OF THE DISCLOSURE

 A semiconductor device comprises at least a
semiconductor layer including source and drain areas
of a first conductive type and of a high impurity
5 concentration and a channel area positioned between
the source and drain areas, an insulation layer
covering at least the channel area, and a gate
electrode positioned close to the insulation layer.
The channel area at least comprises a first channel
10 area of a low resistance, positioned close to the
insulation layer and having a second conductive type
opposite to the first conductive type, and a second
channel area of a high resistance, having the first
conductive type and positioned adjacent to the first
15 channel area.

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